2SC4629

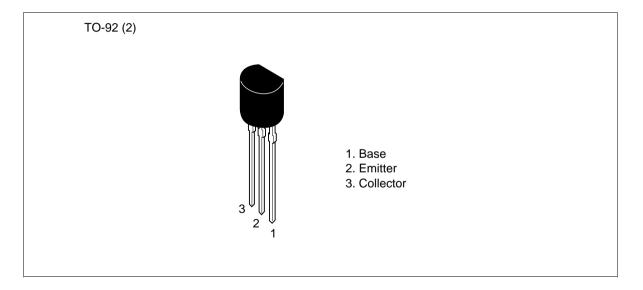
Silicon NPN Epitaxial

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Application

UHF / VHF wide band amplifier

Outline





2SC4629

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

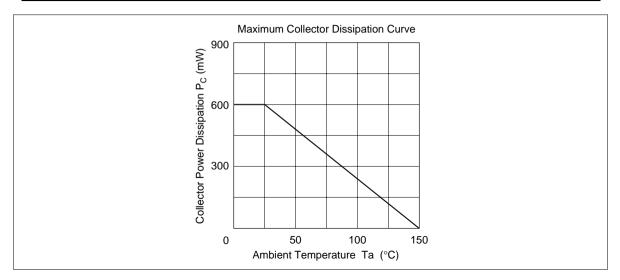
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	15	V
Collector to emitter voltage	V _{CEO}	9	V
Emitter to base voltage	V _{EBO}	1.5	V
Collector current	Ι _c	50	mA
Collector power dissipation	Pc	600	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

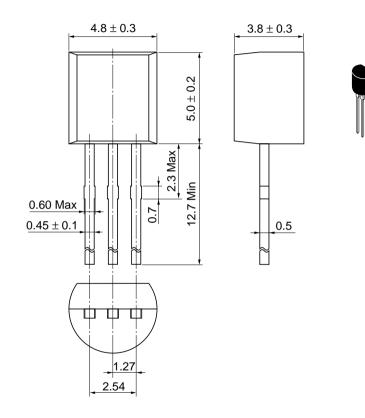
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	—	—	1	μΑ	$V_{CB} = 12 \text{ V}, \text{ I}_{E} = 0$
	I _{CEO}	—	_	1	mA	$V_{ce} = 9 V, R_{be} = \infty$
Emitter cutoff current	I _{EBO}	_		10	μΑ	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	\mathbf{h}_{FE}	40	120	250	—	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA}$
Collector output capacitance	Cob	_	1.15	1.85	pF	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0,$ f = 1MHz
Gain bandwidth product	f _T	5.5	8.0	—	GHz	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA}$
Power gain	PG	8.5	11.5	—	dB	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.2	25	dB	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 5 \text{ mA},$ f = 900 MHz

See characteristic curve of 2SC4592

2SC4629





Hitachi Code	TO-92 (2)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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